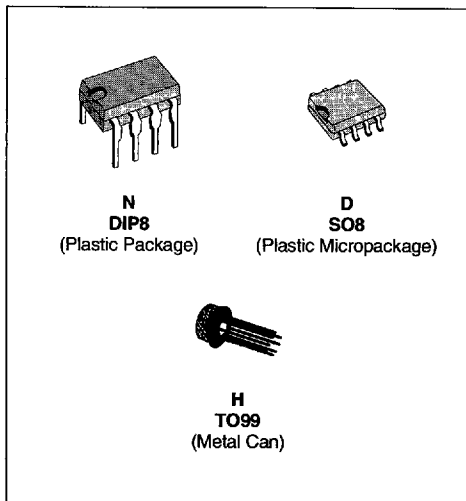


WIDE BANDWIDTH DUAL J-FET OPERATIONAL AMPLIFIERS

- LOW POWER CONSUMPTION
- WIDE COMMON-MODE (UP TO V_{CC}^+) AND DIFFERENTIAL VOLTAGE RANGE
- LOW INPUT BIAS AND OFFSET CURRENT
- OUTPUT SHORT-CIRCUIT PROTECTION
- HIGH INPUT IMPEDANCE J-FET INPUT STAGE
- INTERNAL FREQUENCY COMPENSATION
- LATCH UP FREE OPERATION
- HIGH SLEW RATE : $16V/\mu s$ (typ)



DESCRIPTION

The LF353 are high speed J-FET input dual operational amplifiers incorporating well matched, high voltage J-FET and bipolar transistors in a monolithic integrated circuit.

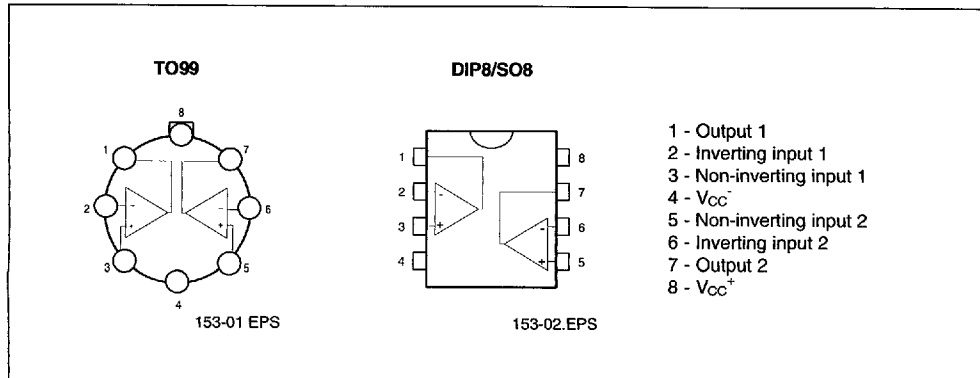
The devices feature high slew rates, low input bias and offset currents, and low offset voltage temperature coefficient.

ORDER CODES

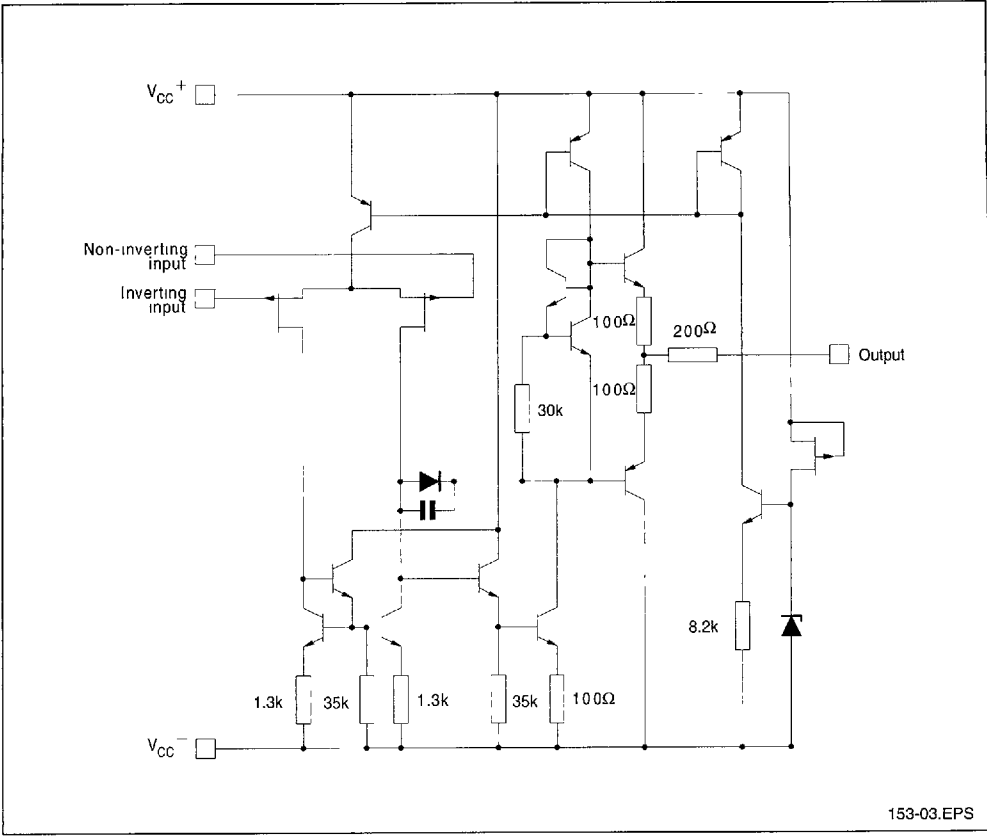
Part Number	Temperature	Package		
		H	N	D
LF353	0°C, +70°C	•	•	•
LF253	-40°C, +105°C	•	•	•
LF153	-55°C, +125°C	•	•	•

153-01.TBL

PIN CONNECTIONS (top views)



SCHEMATIC DIAGRAM (each amplifier)

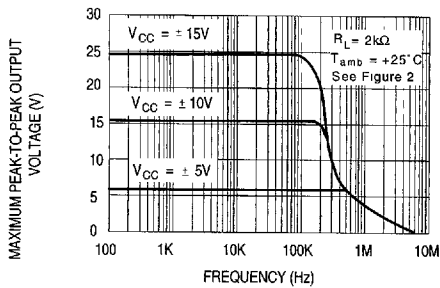


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage - (note 1)	± 18	V
V_i	Input Voltage - (note 3)	± 15	V
V_{id}	Differential Input Voltage - (note 2)	± 30	V
P_{tot}	Power Dissipation	680	mW
	Output Short-circuit Duration - (note 4)	Infinite	
T_{oper}	Operating Free Air Temperature Range	LF353 LF253 LF153	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range		$^{\circ}\text{C}$

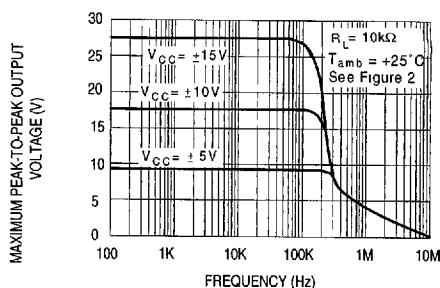
- Notes :
- 1 All voltage values, except differential voltage, are with respect to the zero reference level (ground) of the supply voltages where the zero reference level is the midpoint between V_{CC}^{+} and V_{CC}^{-} .
 - 2 Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal.
 - 3 The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 volts, whichever is less.
 - 4 The output may be shorted to ground or to either supply. Temperature and /or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS FREQUENCY



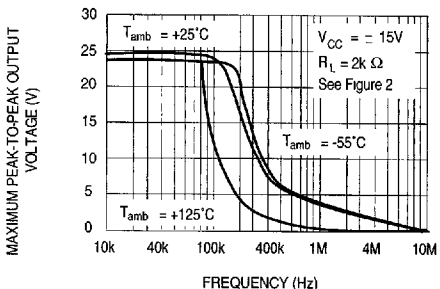
153-04.EPS

MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS FREQUENCY



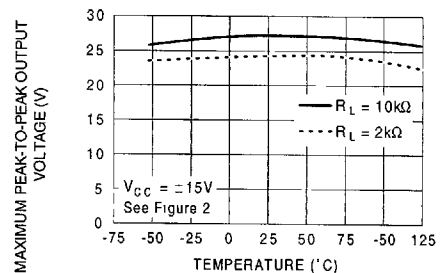
153-05.EPS

MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS FREQUENCY



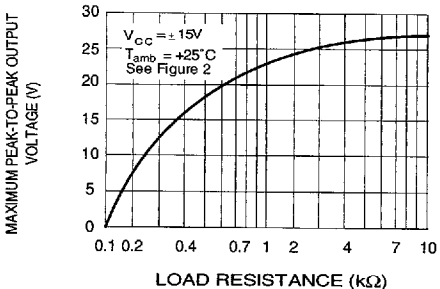
153-06.EPS

MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS FREE AIR TEMP.



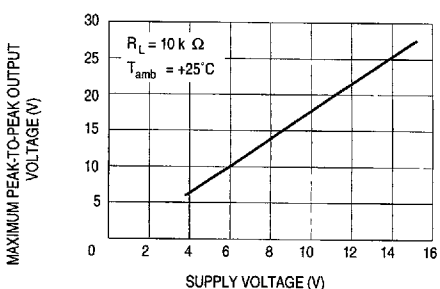
153-07.EPS

MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS LOAD RESISTANCE



153-08.EPS

MAXIMUM PEAK-TO-PEAK OUTPUT
VOLTAGE VERSUS SUPPLY VOLTAGE



153-09.EPS

ELECTRICAL CHARACTERISTICS

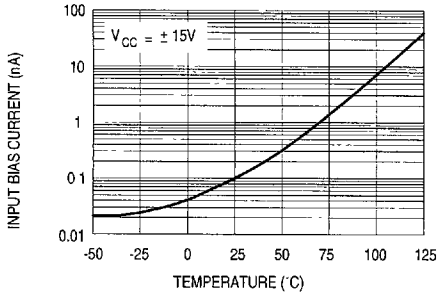
$V_{CC} = \pm 15V$, $T_{amb} = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	LF153 - LF253 - LF353			Unit
		Min.	Typ.	Max.	
V_{io}	Input Offset Voltage ($R_S = 10k\Omega$) $T_{amb} = 25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		3	10 13	mV
DV_{io}	Input Offset Voltage Drift		10		$\mu V/^{\circ}C$
I_{io}	Input Offset Current * $T_{amb} = 25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		5	100 4	pA nA
I_{ib}	Input Bias Current * $T_{amb} = 25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		20	200 20	pA nA
A_{vd}	Large Signal Voltage Gain ($R_L = 2k\Omega$, $V_O = \pm 10V$) $T_{amb} = 25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	50 25	200		V/mV
SVR	Supply Voltage Rejection Ratio ($R_S = 10k\Omega$) $T_{amb} = 25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	80 80	86		dB
I_{cc}	Supply Current, per Amp, no Load $T_{amb} = 25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		1.4	3.2 3.2	mA
V_{icm}	Input Common Mode Voltage Range	± 11	+15 -12		V
CMR	Common Mode Rejection Ratio ($R_S = 10k\Omega$) $T_{amb} = 25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	70 70	86		dB
I_{os}	Output Short-circuit Current $T_{amb} = 25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	10 10	40	60 60	mA
$\pm V_{OPP}$	Output Voltage Swing $T_{amb} = 25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$ $R_L = 2k\Omega$ $R_L = 10k\Omega$ $R_L = 2k\Omega$ $R_L = 10k\Omega$	10 12 10 12	12 13.5		V
SR	Slew Rate ($V_i = 10V$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, unity gain)	12	16		V/ μs
t_r	Rise Time ($V_i = 20mV$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, unity gain)		0.1		μs
K_{OV}	Overshoot ($V_i = 20mV$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, unity gain)		10		%
GBP	Gain Bandwidth Product ($f = 100kHz$, $T_{amb} = 25^{\circ}C$, $V_{in} = 10mV$, $R_L = 2k\Omega$, $C_L = 100pF$)	2.5	4		MHz
R_i	Input Resistance		10^{12}		Ω
THD	Total Harmonic Distortion ($f = 1kHz$, $A_v = 20dB$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, $V_O = 2V_{PP}$)		0.01		%
e_n	Equivalent Input Noise Voltage ($f = 1kHz$, $R_S = 100\Omega$)		15		$\frac{nV}{\sqrt{Hz}}$
ϕ_m	Phase Margin		45		Degrees
V_{O1}/V_{O2}	Channel Separation ($A_v = 100$, $T_{amb} = 25^{\circ}C$)		120		dB

* The input bias currents are junction leakage currents which approximately double for every $10^{\circ}C$ increase in the junction temperature

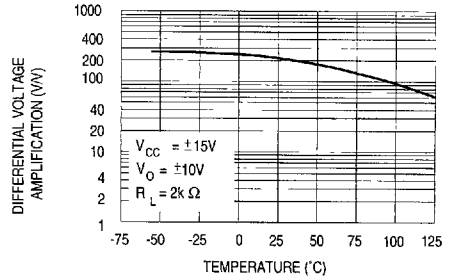
153-03.TBL

INPUT BIAS CURRENT VERSUS FREE AIR TEMPERATURE



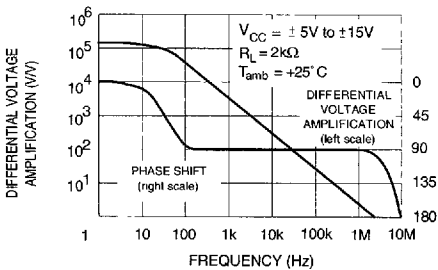
153-10.EPS

LARGE SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION VERSUS FREE AIR TEMPERATURE



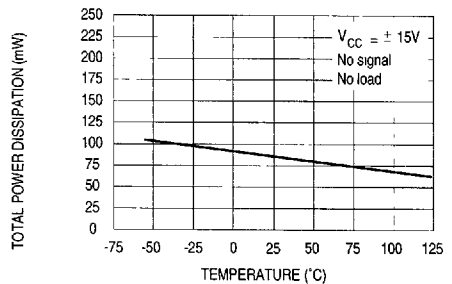
153-11.EPS

LARGE SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT VERSUS FREQUENCY



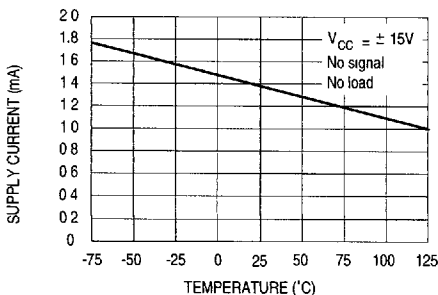
153-12.EPS

TOTAL POWER DISSIPATION VERSUS FREE AIR TEMPERATURE



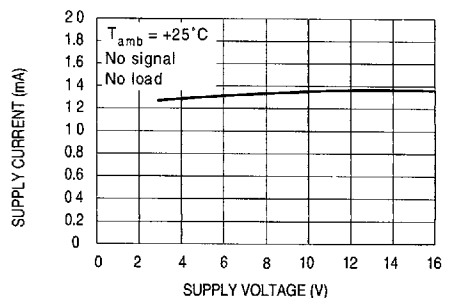
153-13.EPS

SUPPLY CURRENT PER AMPLIFIER VERSUS FREE AIR TEMPERATURE



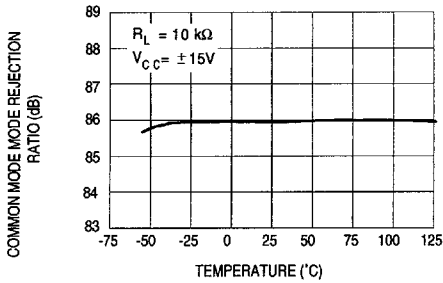
153-14.EPS

SUPPLY CURRENT PER AMPLIFIER VERSUS SUPPLY VOLTAGE



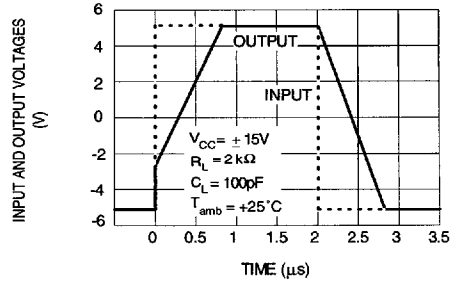
153-15.EPS

COMMON MODE REJECTION RATIO
VERSUS FREE AIR TEMPERATURE



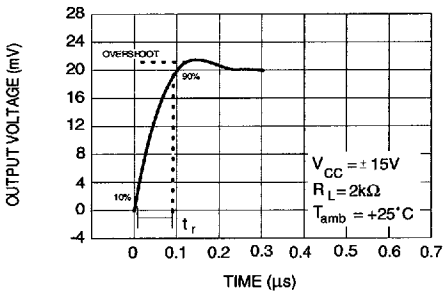
153-16.EPS

VOLTAGE FOLLOWER LARGE SIGNAL
PULSE RESPONSE



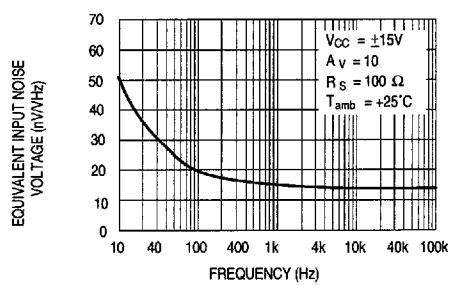
153-17.EPS

OUTPUT VOLTAGE VERSUS
ELAPSED TIME



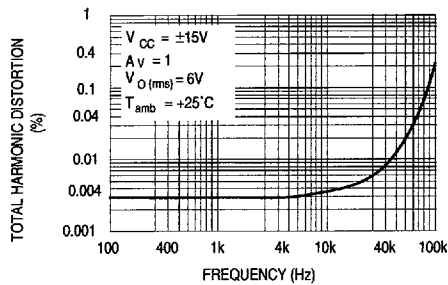
153-18.EPS

EQUIVALENT INPUT NOISE VOLTAGE
VERSUS FREQUENCY



153-19.EPS

TOTAL HARMONIC DISTORTION VERSUS
FREQUENCY



153-20.EPS

PARAMETER MEASUREMENT INFORMATION

Figure 1 : Voltage Follower

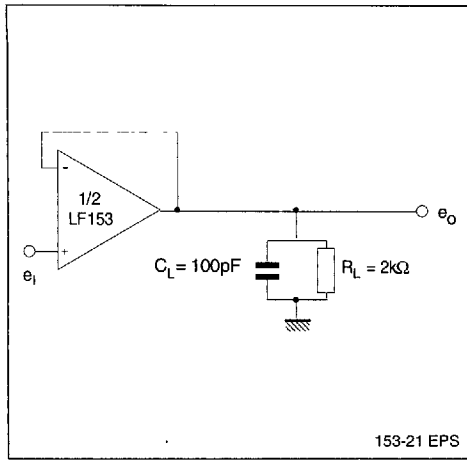
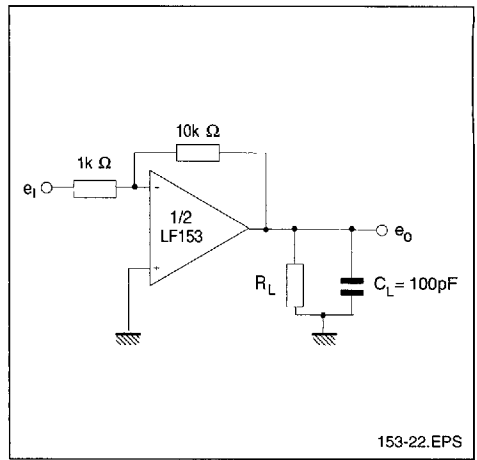


Figure 2 : Gain-of-10 Inverting Amplifier



TYPICAL APPLICATION

QUADRUPLE OSCILLATOR

